

LV30200FCT

Rev.F Mar.-2016

/ Descriptions

TO-220F Schottky Diode in a TO-220F Plastic Package.

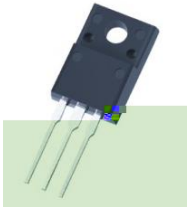
/ Features

Low forward voltage drop, low power losses, High efficiency operation.

/ Applications

OR-ing ; ; ; ;
For use in high frequency inverters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

/ Equivalent Hq56 247 0 .8TD)ET0.70.82 0.05 rg5754 454036.564 1806 ref62.0 74.02036.



PIN1 Anode PIN 2 Cathode PIN 3 Anode

/ h_{FE} Classifications & Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RM} V_{RSM} V_{DC}	200	V
RMS Voltage	V_{RMS}	140	V
Average Rectified Forward Current	$I_{F(AV)}$	2×15	A
Non Repetitive Peak Surge Current	I_{FSM}	200	A
Thermal Resistance Junction to Case	R_{Jc}	4.6	/W
Junction and Storage Temperature Range	T_j T_{stg}	-40 +150	

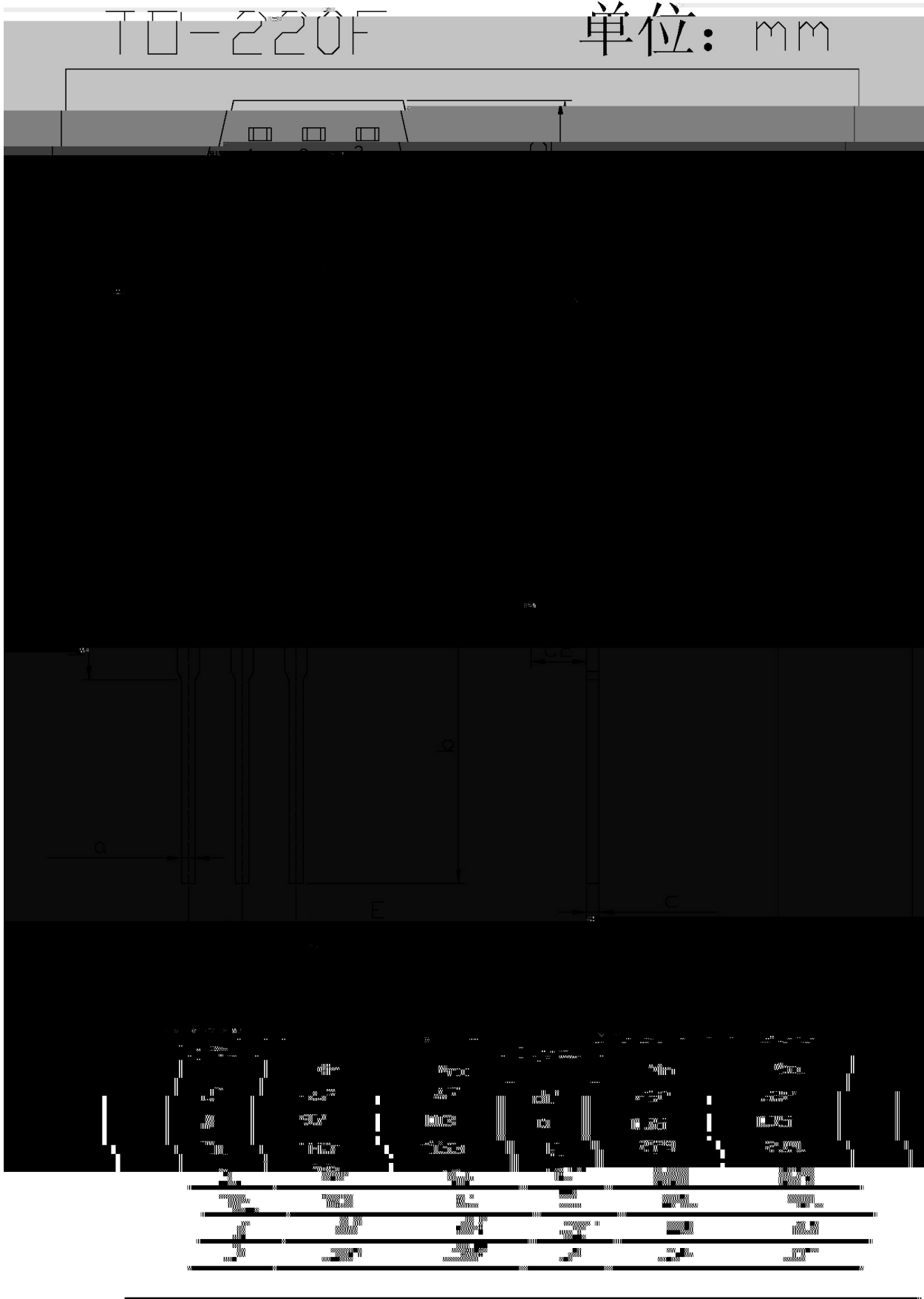
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Breakdown Voltage	V_{BR}	$I_R=1mA(Ta=25)$	200			V
Forward Voltage	V_F	$I_F=5A(Ta=25)$		0.73	0.85	V
		$I_F=10A(Ta=25)$		0.80	0.95	V
		$I_F=15A(Ta=25)$		0.92	1.15	V
		$I_F=5A(Ta=125)$		0.58		V
		$I_F=10A(Ta=125)$		0.66		V
		$I_F=15A(Ta=125)$		0.71	0.85	V
Instantaneous Reverse Current	I_R Note 1	$V_R=200V(Ta=25)$		4	20	μA
		$V_R=200V(Ta=125)$		5	10	mA

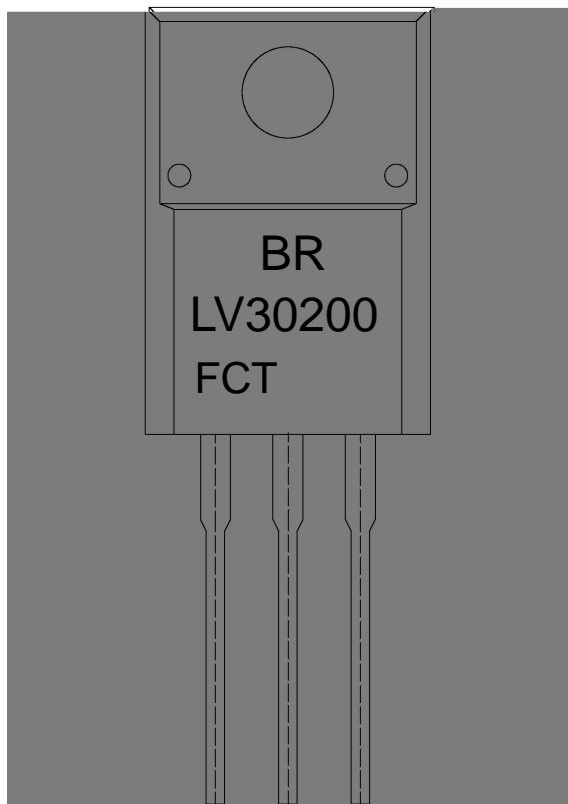
/Notes

1. /Short duration pulse test used to minimize self-heating effect.
2. / Unless otherwise noted, values for the parameters of a single chip

/ Package



/ Marking Instructions



9R

LV*O) 00

F:

: T:

Note:

BR: Company Code

LV*O) 00 Product Type.

F: Package Code

: T: Internal Structure

****: Lot No. Code, code change with Lot No.

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